FLASH-ROM MODULE 4MByte (1M x 32-Bit), 72pin-SIMM, 5V
Part No. HMF1M32M8G

GENERAL DESCRIPTION

The HMF1M32M8G is a high-speed flash read only memory (FROM) module containing 1,048,576 words organized in a x32bit configuration. The module consists of eight 512K x 8 FROM mounted on a 72-pin, single-sided, FR4-printed circuit board. Commands are written to the command register using standard microprocessor write timings.
Register contents serve as input to an internal state-machine, which controls the erase and programming circuitry. Write cycles also internally latch addresses and data needed for the programming and erase operations. Reading data out of the device is similar to reading from 12.0V flash or EPROM devices.

Eight chip enable inputs, (/CE_UU1, /CE_UM1, /CE_LM1, /CE_LL1, /CE_UU2, /CE_UM2, /CE_LM2, /CE_LL2) are used to enable the module's 4 bytes independently. Output enable (/OE) and write enable (/WE) can set the memory input and output..When FROM module is disable condition the module is becoming power standby mode, system designer can get low-power design. All module components may be powered from a single +5V DC power supply and all inputs and outputs are TTL-compatible.

FEATURES

- Access time: 55, 70, 90 and 120ns
- High-density 4MByte design
- High-reliability, low-power design
- Single + 5V ± 0.5V power supply
- Easy memory expansion
- All inputs and outputs are TTL-compatible
- FR4-PCB design
- Low profile 72-pin SIMM
- Minimum 1,000,000 write/erase cycle
- Sector erases architecture
- Sector group protection
- Temporary sector group unprotection

OPTIONS MARKING

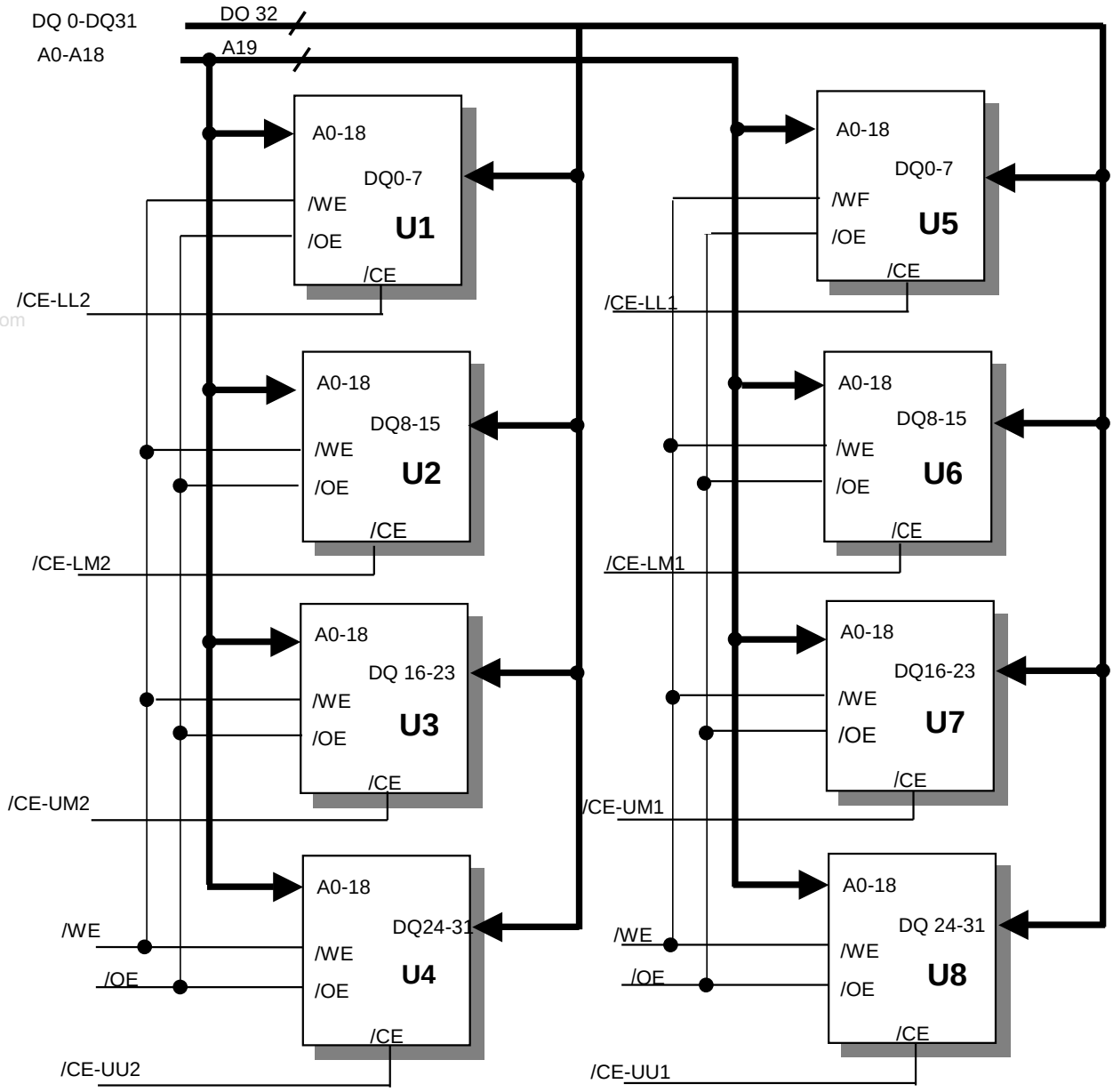
- Timing
  - 55ns access -55
  - 70ns access -70
  - 90ns access -90
  - 120ns access -120
- Packages
  - 72-pin SIMM M

PIN ASSIGNMENT

PIN	SYMBOL	PIN	SYMBOL	PIN	SYMBOL
1	Vss	25	Vcc	49	DQ17
2	A3	26	DQ8	50	DQ18
3	A2	27	DQ9	51	DQ22
4	A1	28	DQ10	52	DQ21
5	A0	29	/CE_LM2	53	DQ20
6	Vcc	30	Vcc	54	DQ19
7	A11	31	/CE_LM1	55	Vcc
8	/OE	32	DQ15	56	A15
9	A10	33	DQ14	57	A12
10	Vcc	34	DQ13	58	A7
11	/CE_LL2	35	DQ12	59	Vcc
12	/CE_LL1	36	DQ11	60	A8
13	DQ7	37	A18	61	A9
14	DQ0	38	A16	62	DQ24
15	DQ1	39	Vss	63	DQ25
16	DQ2	40	A6	64	DQ26
17	DQ6	41	Vcc	65	/CE_UU2
18	DQ5	42	A5	66	/CE_UU1
19	DQ4	43	A4	67	DQ31
20	DQ3	44	Vcc	68	DQ30
21	/WE	45	/CE_UM2	69	DQ29
22	A17	46	/CE_UM1	70	DQ28
23	A14	47	DQ23	71	DQ27
24	A13	48	DQ16	72	Vss

72-PIN SIMM
TOP VIEW

FUNCTIONAL BLOCK DIAGRAM



TRUTH TABLE

MODE	/OE	/CE	/WE	DQ	POWER
STANDBY	X	H	X	HIGH-Z	STANDBY
NOT SELECTED	H	L	H	HIGH-Z	ACTIVE
READ	L	L	H	Q	ACTIVE
WRITE or ERASE	X	L	L	D	ACTIVE

NOTE: X means don't care

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING
Voltage with respect to ground all other pins	$V_{IN,OUT}$	-2.0V to +7.0V
Voltage with respect to ground Vcc	V_{CC}	-2.0V to +7.0V
Storage Temperature	T_{STG}	-65°C to +125°C
Operating Temperature	T_A	-55°C to +125°C

w Stresses greater than those listed under " Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions ab ove those indicated in the operating section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS

PARAMETER	SYMBOL	MIN	TYP.	MAX
Vcc for ±5% device Supply Voltages	V_{CC}	4.75V		5.25V
Vcc for ± 10% device Supply Voltages	Vcc	4.5V		5.5V
Ground	V_{SS}	0	0	0

DC AND OPERATING CHARACTERISTICS ($0^oC \le T_A \le 70\ ^oC$; Vcc = 5V ± 0.5V)

PARAMETER	TEST CONDITIONS	SYMBOL	MIN	MAX	UNITS
Input Leakage Current	Vcc=Vcc max, V_{IN}= GND to Vcc	I_{L1}		±1.0	µA
Output Leakage Current	Vcc=Vcc max, VOUT= GND to Vcc	I_{L0}		±1.0	µA
Output High Voltage	I_{OH} = -2.5mA, Vcc = Vcc min	V_{OH}	2.4		V
Output Low Voltage	I_{OL} = 12mA, Vcc =Vcc min	V_{OL}		0.45	V
Vcc Active Current for Read(1)	/CE = V_{IL}, /OE=V_{IH},	I_{CC1}		12	mA
Vcc Active Current for Program or Erase(2)	/CE = V_{IL}, /OE=V_{IH}	I_{CC2}		40	mA
Vcc Standby Current	/CE= V_{IH}	I_{CC3}		1.0	mA
Low Vcc Lock-Out Voltage		V_{LKO}	3.2	4.2	V

Notes:

1. The Icc current listed is typically less than 2mA/MHz, with /OE at V_{IH}.
2. Icc active while embedded algorithm (program or erase) is in progress
3. Maximum Icc current specifications are tested with Vcc=Vcc max

ERASE AND PROGRAMMING PERFORMANCE

PARAMETER	LIMITS			UNIT	COMMENTS
	MIN.	TYP.	MAX.		
Sector Erase Time	-	1	8	sec	Excludes 00H programming prior to erasure
Byte Programming Time	-	7	300	µs	Excludes system-level overhead
Chip Programming Time	-	3.6	10.8	sec	Excludes system-level overhead

CAPACITANCE

PARAMETER SYMBOL	PARAMETER DESCRIPTION	TEST SETUP	TYP.	MAX	UNIT
C_{IN}	Input Capacitance	V_{IN} = 0	4	6	pF
C_{OUT}	Output Capacitance	V_{OUT} = 0	8	12	pF
C_{IN2}	Control Pin Capacitance	V_{IN} = 0	8	12	pF

Notes : Test conditions T_A = 25°C, f=1.0 MHz.

AC CHARACTERISTICS

u Read Only Operations Characteristics

PARAMETER SYMBOLS		DESCRIPTION	TEST SETUP		-55	-90	UNIT
JEDEC	STANDARD						
t_{AVAV}	t_{RC}	Read Cycle Time		Min	55	90	ns
t_{AVQV}	t_{ACC}	Address to Output Delay	/CE = V_{IL} /OE = V_{IL}	Max	55	90	ns
t_{ELQV}	t_{CE}	Chip Enable to Output Delay	/OE = V_{IL}	Max	55	90	ns
t_{GLQV}	t_{OE}	Chip Enable to Output Delay		Max	30	35	ns
t_{EHQZ}	t_{DF}	Chip Enable to Output High-Z		Max	18	20	ns
t_{GHQZ}	t_{DF}	Output Enable to Output High-Z		Max	18	20	ns
t_{AXQX}	t_{OH}	Output Hold Time From Addresses, /CE or /OE, Whichever Occurs First		Min	0	0	ns

Notes : Test Conditions : Output Load : 1TTL gate and Output Load Capacitance 100 pF, in case of 55ns-30pF

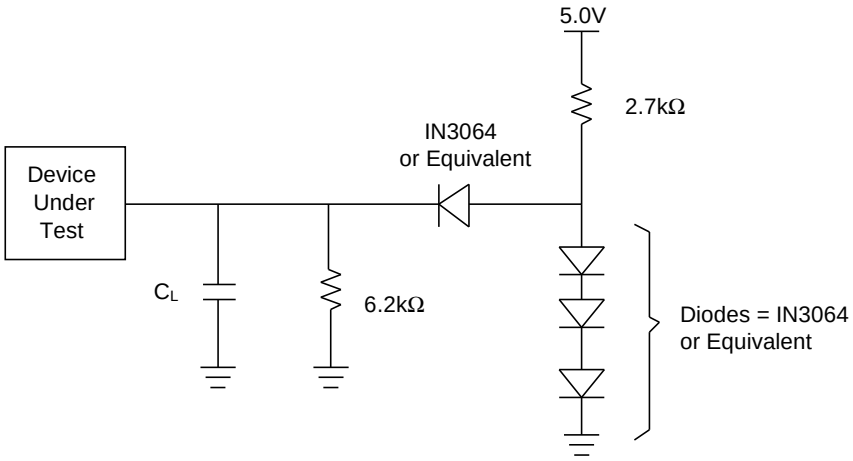
Input rise and fall times : 5 ns, In case of 55ns-5ns

Input pulse levels : 0 .45V to 2.4V, In case of 55ns- 0.0V-3.0V

Timing measurement reference level

Input : 0.8V, Incase of 55ns-1.5V

Output : 2.0V, In case of 55ns-1.5V



Note : C_L = 100pF including jig capacitance

u Erase/Program Operations

PARAMETER SYMBOLS		DESCRIPTION		-55	-90	UNIT
JEDEC	STANDARD					
t_{AVAV}	t_{WC}	Write Cycle Time	Min	55	90	ns
t_{AVWL}	t_{AS}	Address Setup Time	Min	0	0	ns
t_{WLAX}	t_{AH}	Address Hold Time	Min	40	45	ns
t_{DVWH}	t_{DS}	Data Setup Time	Min	25	45	ns
t_{WHDX}	t_{DH}	Data Hold Time	Min	0	0	ns
	t_{OES}	Output Enable Setup Time	Min	0	0	ns
t_{GHWL}	t_{GHWL}	Read Recover Time Before Write	Min	0	0	ns
t_{ELWL}	t_{CS}	/CE Setup Time	Min	0	0	ns
t_{WHEH}	t_{CH}	/CE Hold Time	Min	0	0	ns
t_{WLWH}	t_{WP}	Write Pulse Width	Min	30	45	ns
t_{WHWL}	t_{WPH}	Write Pulse Width High	Min	20	20	ns
t_{WHWH1}	t_{WHWH1}	Byte Programming Operation	Typ	7	7	µs
t_{WHWH2}	t_{WHWH2}	Sector Erase Operation (Note1)	Typ	1	1	sec
	t_{VCS}	Vcc set up time	Min	50	50	µs

Notes :

1. This does not include the preprogramming time
2. This timing is only for Sector Protect operations

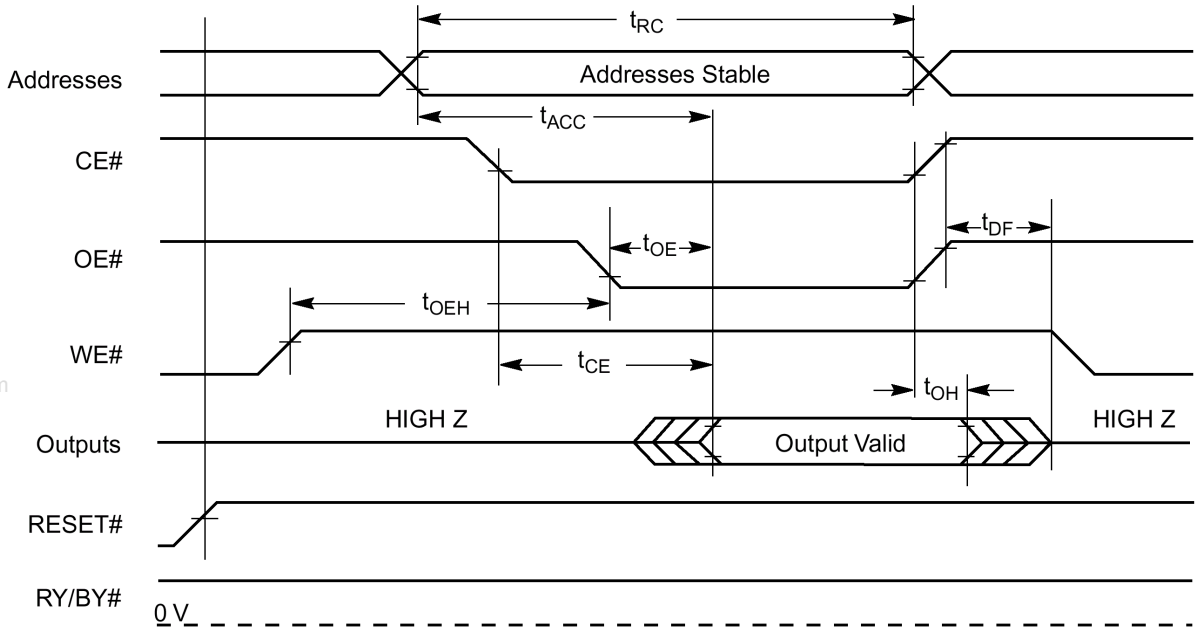
u Erase/Program Operations

Alternate /CE Controlled Writes

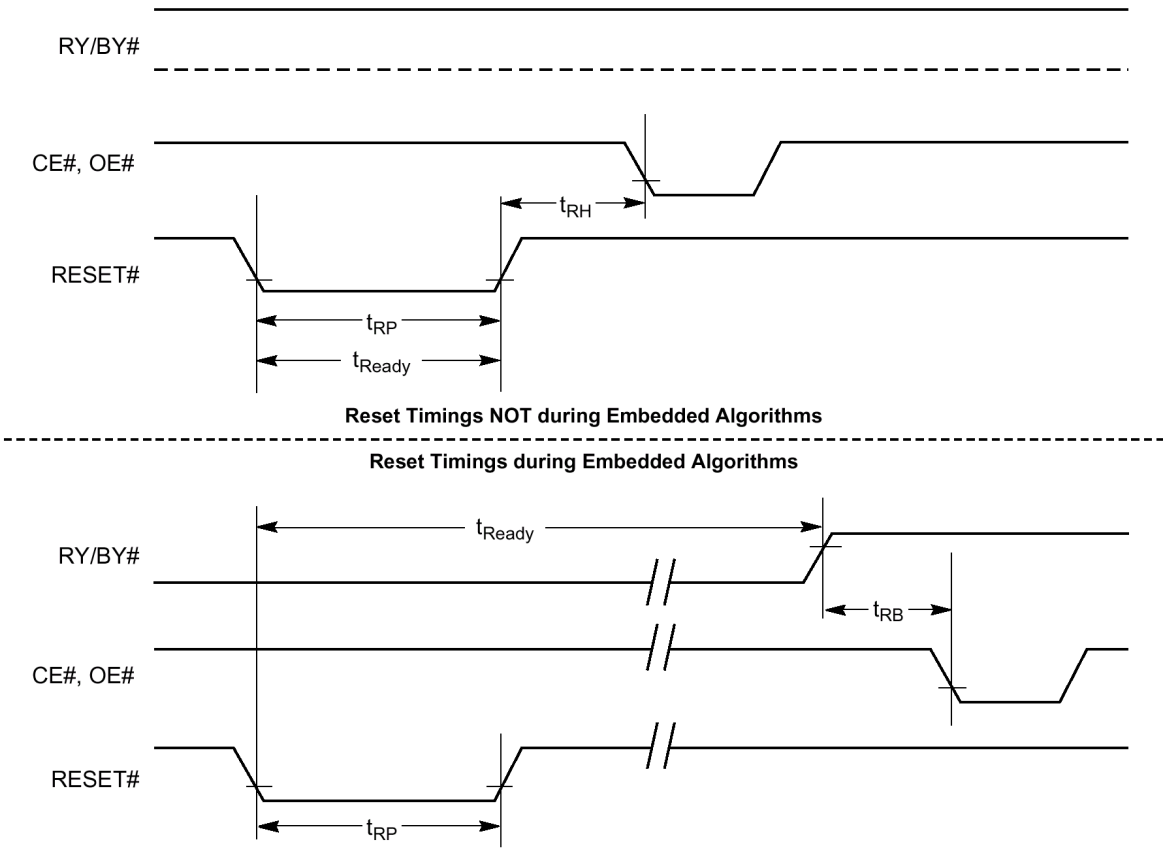
PARAMETER SYMBOLS		DESCRIPTION		-55	-90	UNIT
JEDEC	STANDARD					
t_{AVAV}	t_{WC}	Write Cycle Time	Min	55	90	ns
t_{AVEL}	t_{AS}	Address Setup Time	Min	0	0	ns
t_{ELAX}	t_{AH}	Address Hold Time	Min	40	45	ns
t_{DVEH}	t_{DS}	Data Setup Time	Min	25	45	ns
t_{EHDX}	t_{DH}	Data Hold Time	Min	0	0	ns
	t_{OES}	Output Enable Setup Time	Min	0	0	ns
t_{GHEL}	t_{GHEL}	Read Recover Time Before Write	Min	0	0	ns
t_{WLEL}	t_{WS}	/WE Setup Time	Min	0	0	ns
t_{EHWH}	t_{WH}	/WE Hold Time	Min	0	0	ns
t_{ELEH}	t_{CP}	/CE Pulse Width	Min	30	45	ns
t_{EHEL}	t_{CPH}	/CE Pulse Width High	Min	20	20	ns
t_{WHWH1}	t_{WHWH1}	Byte Programming Operation	Typ	7	7	µs
t_{WHWH2}	t_{WHWH2}	Sector Erase Operation (Note)	Typ	1	1	sec

Notes : This does not include the preprogramming time.

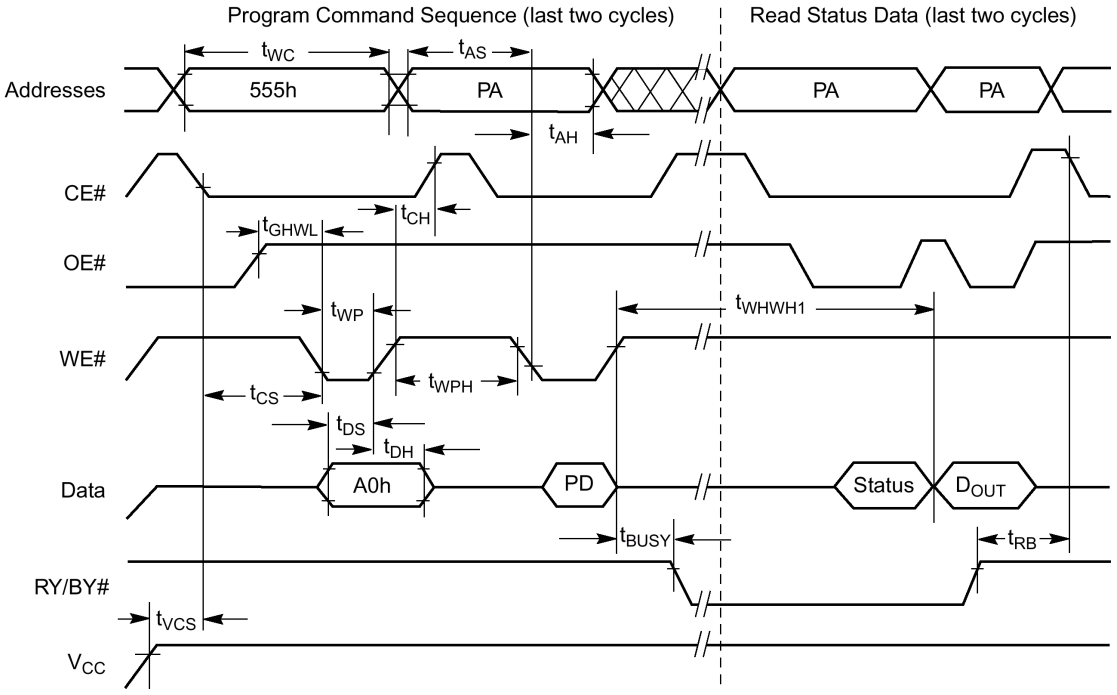
u READ OPERATIONS TIMING



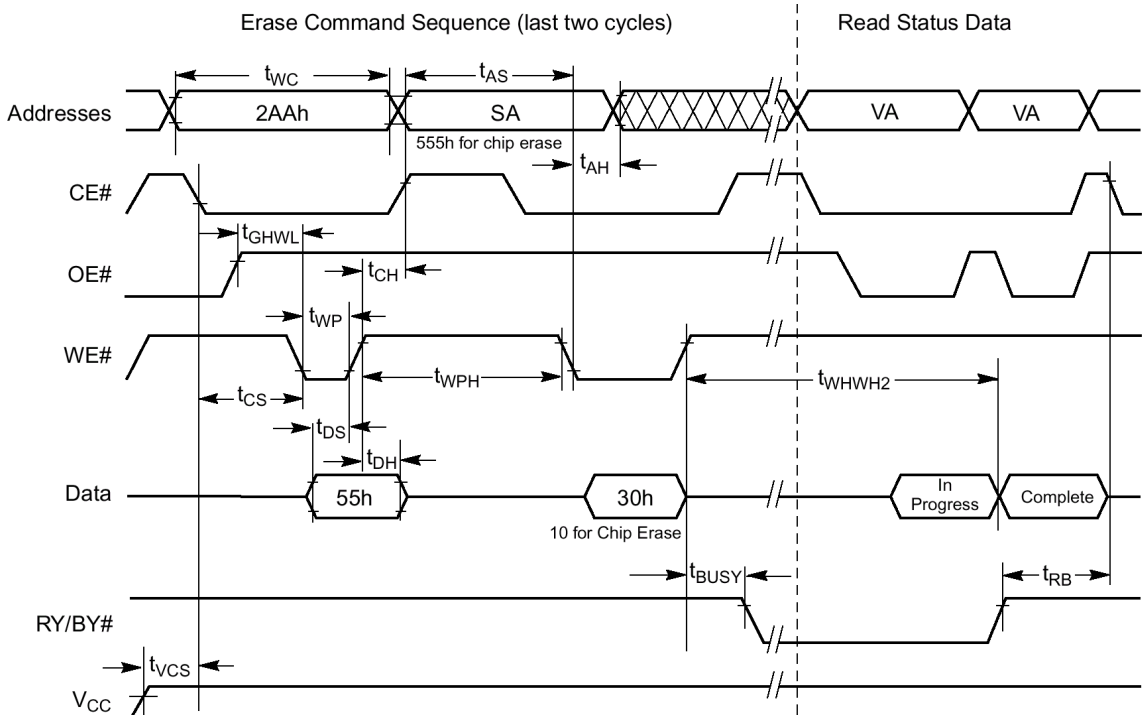
u RESET TIMING



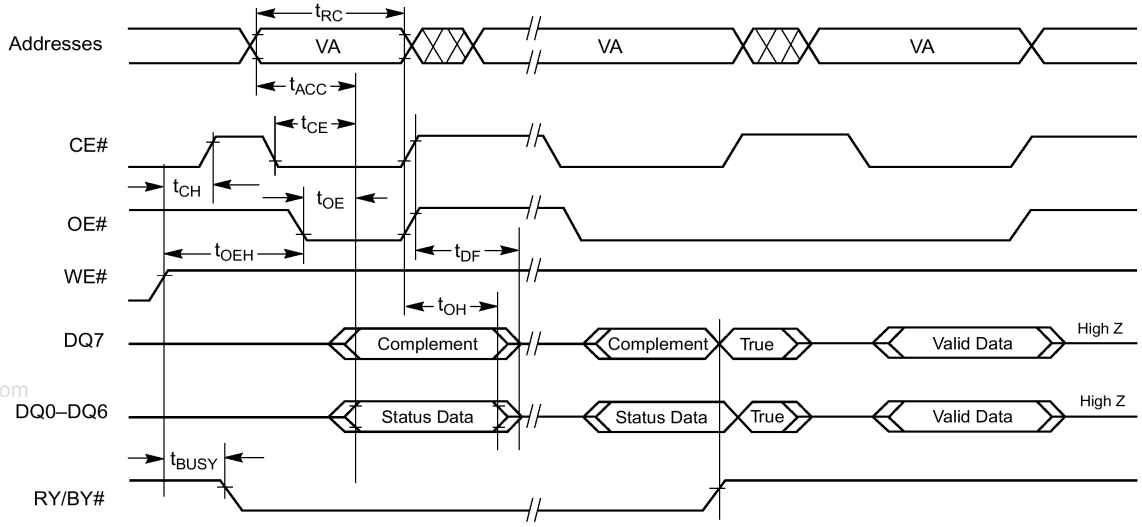
u PROGRAM OPERATIONS TIMING



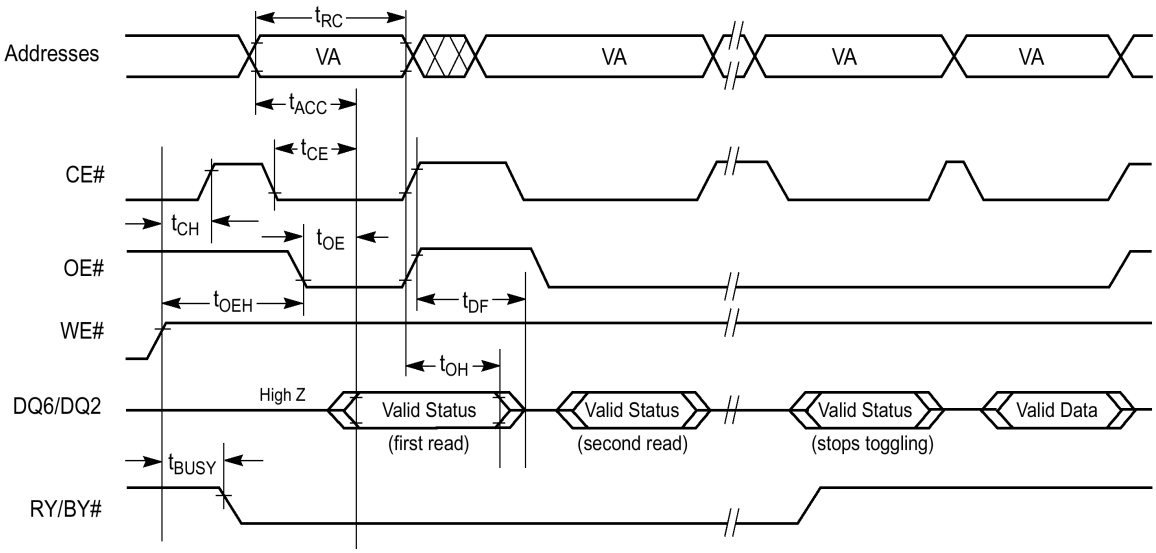
u CHIP/SECTOR ERASE OPERATION TIMINGS



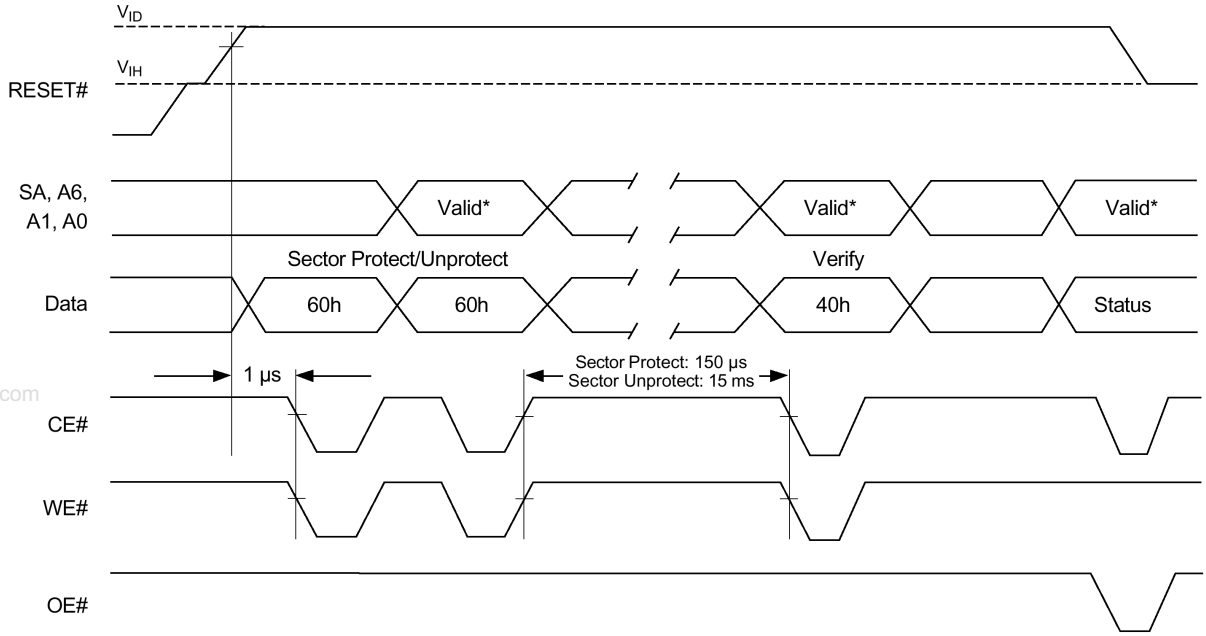
u DATA# POLLING TIMES(DURING EMBEDDED ALGORITHMS)



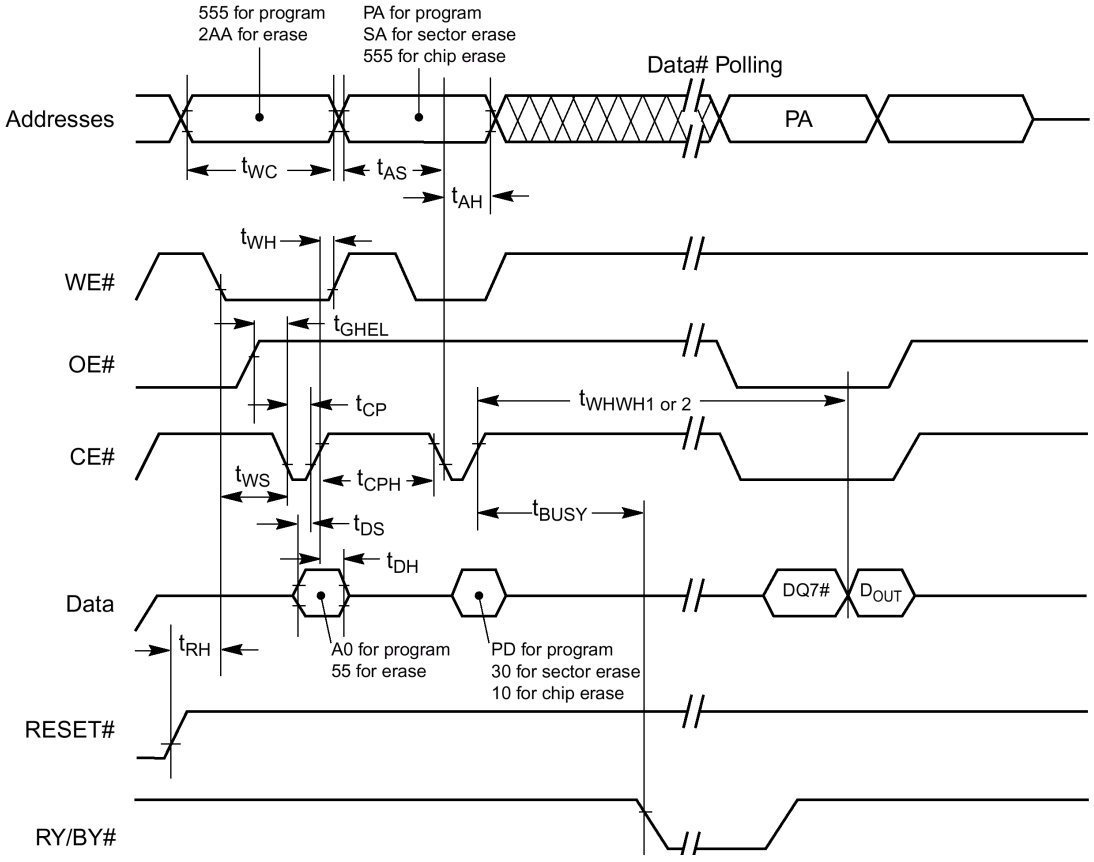
u TOGGLE# BIT TIMINGS (DURING EMBEDDED ALGORITHMS)



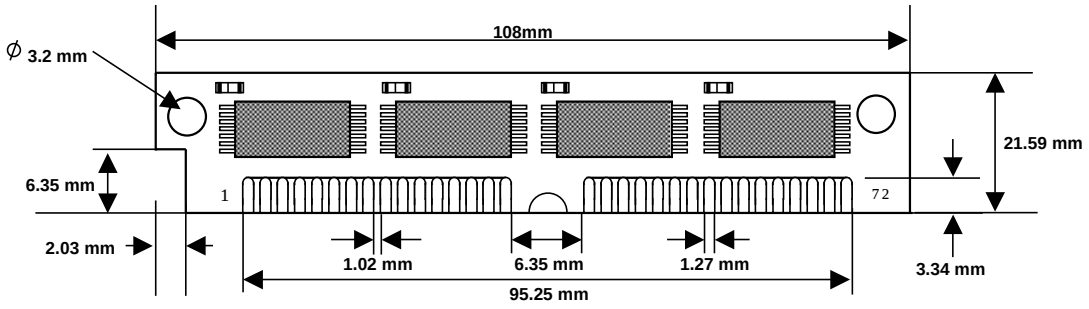
u SECTOR PROTECT UNPROTECT TIMEING DIAGRAM

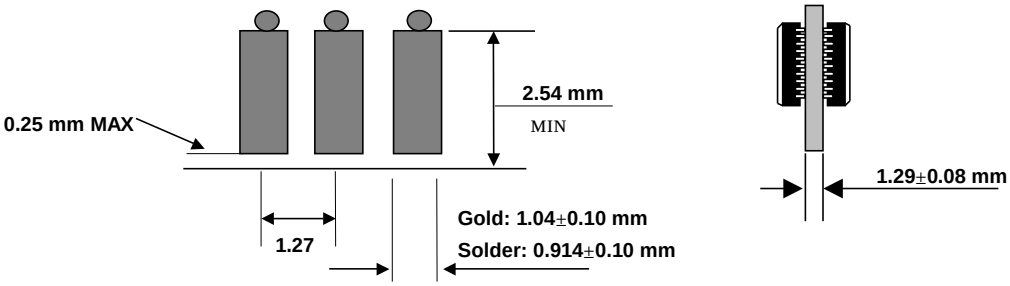


u ALTERNATE CE# CONTROLLED WRITE OPERATING TIMINGS



PACKAGE DIMENSIONS





(Solder & Gold Plating)

ORDERING INFORMATION

Part Number	Density	Org.	Package	Component Number	Vcc	SPEED
HMF1M32M8G-55	4MByte	1M×32bit	72pin-SIMM	8EA	5.0V	55ns
HMF1M32M8G-70	4MByte	1M×32bit	72pin-SIMM	8EA	5.0V	70ns
HMF1M32M8G-90	4MByte	1M×32bit	72pin-SIMM	8EA	5.0V	90ns
HMF1M32M8G-120	4MByte	1M×32bit	72pin-SIMM	8EA	5.0V	120ns